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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LCD, LVD, POR, PWM, WDT
Number of I/O	37
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 10x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	52-LQFP
Supplier Device Package	52-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f10rjagfa-x0

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Pin count	Package	Fields of	Part Number
	U U	Application Note	
32 pins	32-pin plastic LQFP (7 \times 7)	А	R5F10RB8AFP, R5F10RBAAFP, R5F10RBCAFP
		G	R5F10RB8GFP, R5F10RBAGFP, R5F10RBCGFP
44 pins	44-pin plastic LQFP (10 $ imes$ 10)	А	R5F10RF8AFP, R5F10RFAAFP, R5F10RFCAFP
		G	R5F10RF8GFP, R5F10RFAGFP, R5F10RFCGFP
48 pins	48-pin plastic LQFP (fine pitch)	А	R5F10RG8AFB, R5F10RGAAFB, R5F10RGCAFB
	(7 × 7)	G	R5F10RG8GFB, R5F10RGAGFB, R5F10RGCGFB
52 pins	52-pin plastic LQFP (10 $ imes$ 10)	А	R5F10RJ8AFA, R5F10RJAAFA, R5F10RJCAFA
		G	R5F10RJ8GFA, R5F10RJAGFA, R5F10RJCGFA
64 pins	64-pin plastic WQFN (8 $ imes$ 8)	А	R5F10RLAANB, R5F10RLCANB
		G	R5F10RLAGNB, R5F10RLCGNB
	64-pin plastic LQFP (fine pitch)	А	R5F10RLAAFB, R5F10RLCAFB
	(10 × 10)	G	R5F10RLAGFB, R5F10RLCGFB
	64-pin plastic LQFP (12 $ imes$ 12)	А	R5F10RLAAFA, R5F10RLCAFA
		G	R5F10RLAGFA, R5F10RLCGFA

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/L12.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



1.5.3 48-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR)

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1.5.4 52-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR)

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1.6 Outline of Functions

RL78/L12

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

						(1/2)				
	Item	32-pin	44-pin	48-pin	52-pin	64-pin				
		R5F10RBx	R5F10RFx	R5F10RGx	R5F10RJx	R5F10RLx				
Code flash	n memory (KB)	8 to 32	8 to 32	8 to 32	8 to 32	16, 32				
Data flash	memory (KB)	2	2	2	2	2				
RAM (KB)		1, 1.5 ^{Note 1}	1, 1.5 ^{Note 1}	1, 1.5 ^{Note 1}	1, 1.5 ^{Note 1}	1, 1.5 ^{Note 1}				
Memory s	bace	1 MB								
Main High-speed system clock X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) system HS (high-speed main) operation: 1 to 20 MHz (V _{DD} = 2.7 to 5.5 V), clock HS (high-speed main) operation: 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V), LS (low-speed main) operation: 1 to 8 MHz (V _{DD} = 1.8 to 5.5 V), LV (low-voltage main) operation: 1 to 4 MHz (V _{DD} = 1.6 to 5.5 V)										
	High-speed on-chip oscillator clock	HS (high-speed HS (high-speed LS (low-speed r LV (low-voltage	\dot{S} (high-speed main) operation: 1 to 24 MHz (V _{DD} = 2.7 to 5.5 V), \dot{S} (high-speed main) operation: 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V), \dot{S} (low-speed main) operation: 1 to 8 MHz (V _{DD} = 1.8 to 5.5 V), \prime (low-voltage main) operation: 1 to 4 MHz (V _{DD} = 1.6 to 5.5 V)							
Subsystem clock - XT1 (crystal) oscillation , external subsystem clock input (EX0 32.768 kHz (TYP.): VDD = 1.6 to 5.5 V					input (EXCLKS)					
Low-speed on-chip oscillator clock Internal oscillation 15 kHz (TYP.): VDD = 1.6 to 5.5 V										
General-p	urpose register	8 bits \times 32 regis	sters (8 bits $ imes$ 8 r	egisters $ imes$ 4 bank	s)					
Minimum i	nstruction execution time	0.04167 <i>μ</i> s (Hig	gh-speed on-chip	oscillator clock:	fін = 24 MHz ope	eration)				
		0.05 μ s (High-speed system clock: f _{MX} = 20 MHz operation)								
		30.5 µs (Subsystem clock: fsue = 32.768 kHz operation)								
Instruction	set	 Data transfer Adder and su Multiplication Rotate, barre operation), et 	(8/16 bits) $ibtractor/logical c (8 bits \times 8 bits)I shift, and bit matc.$	operation (8/16 bi anipulation (Set, r	ts) reset, test, and E	Boolean				
Total num pins dedic	ber of I/O port pins and ated to drive an LCD	28	40	44	48	58				
I/O port	Total	20	29	33	37	47				
	CMOS I/O	15	22	26	30	39				
	CMOS input	3	5	5	5	5				
	CMOS output	_	_	-	_	1				
	N-ch open-drain I/O (EV _{DD} tolerance)	2	2	2	2	2				
Pins d	edicated to drive an LCD	8	11	11	11	11				
LCD contr	oller/driver	Internal voltage division method	boosting method are switchable.	d, capacitor split	method, and ext	ernal resistance				
	Segment signal output	13	22 (18) Note 2	26 (22) Note 2	30 (26) Note 2	39 (35) Note 2				
	Common signal output	4		4 (8)	Note 2					

Notes 1. In the case of the 1 KB, and 1.5 KB, this is 630 bytes when the self-programming function and data flash function is used.

2. The values in parentheses are the number of signal outputs when 8 com is used.

Items	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Output current, Iow ^{Note 1}	Iol1	Per pin for P10 to P17, P30 to P32, P40 to P43, P50 to P54, P70 to P74, P120, P125 to P127, P130, P140 to P147					20.0 Note 2	mA
		Per pin for	P60, P61				15.0 Note 2	mA
		Total of P1	0 to P14, P40 to P43,	$4.0~V \leq EV_{\text{DD}} \leq 5.5~V$			70.0	mA
		P120, P130, P140 to P147 (When duty = 70% ^{Note 3})		$2.7~V \leq EV_{\text{DD}} < 4.0~V$			15.0	mA
				$1.8~V \leq EV_{\text{DD}} < 2.7~V$			9.0	mA
				$1.6~V \leq EV_{\text{DD}} < 1.8~V$			4.5	mA
		Total of P1	5 to P17, P30 to P32,	$4.0~V \leq EV_{\text{DD}} \leq 5.5~V$			80.0	mA
		P50 to P54, P60, P6 P125 to P127 (When duty = 70% [№]	I, P60, P61, P70 to P74,	$2.7~V \leq EV_{\text{DD}} < 4.0~V$			35.0	mA
			$v = 70\%^{\text{Note 3}}$	$1.8~V \leq EV_{\text{DD}} < 2.7~V$			20.0	mA
		($1.6~V \leq EV_{\text{DD}} < 1.8~V$			10.0	mA
		Total of all (When dut	pins y = 70% ^{Note 3})				150.0	mA
	IOL2 P20, P21	P20, P21	Per pin	Per pin			0.4	mA
			Total of all pins	$1.6~V \leq V_{\text{DD}} \leq 5.5~V$			0.8	mA

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{\text{DD}} = \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{ Vss} = \text{EV}_{\text{SS}} = 0 \text{ V})$



- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from the V_{DD} and EV_{DD} pins to an output pin.
 - 2. Do not exceed the total current value.
 - **3.** Specification under conditions where the duty factor \leq 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = $(I_{OH} \times 0.7)/(n \times 0.01)$
- <Example> Where n = 80% and IoL = 70.0 mA

Total output current of pins = $(70.0 \times 0.7)/(80 \times 0.01) \cong 61.25$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



- Notes 1. Current flowing to VDD.
 - 2. When high speed on-chip oscillator and high-speed system clock are stopped.
 - 3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.
 - 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
 - 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer is in operation.
 - 6. Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
 - 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
 - 8. Current flowing only during data flash rewrite.
 - 9. Current flowing only during self programming.
 - **10.** For shift time to the SNOOZE mod.
 - 11. Current flowing only to the LCD controller/driver. The supply current value of the RL78 microcontrollers is the sum of the LCD operating current (ILCD1, ILCD2 or ILCD3) to the supply current (IDD1 or IDD2) when the LCD controller/driver operates in an operation mode or HALT mode. Not including the current that flows through the LCD panel.

The TYP. value and MAX. value are following conditions.

- When fsuB is selected for system clock, LCD clock = 128 Hz (LCDC0 = 07H)
- 4-Time-Slice, 1/3 Bias Method
- **12.** Not including the current that flows through the external divider resistor when the external resistance division method is used.
- Remarks 1. fil: Low-speed on-chip oscillator clock frequency
 - 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 3. fcLK: CPU/peripheral hardware clock frequency
 - 4. Temperature condition of the TYP. value is T_A = 25°C





CSI mode connection diagram (during communication at same potential)





CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)





2. m: Unit number, n: Channel number (mn = 00, 01)



(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (3/3) $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{\text{DD}} = \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{ Vss} = \text{EV}_{\text{Ss}} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-	LS (low-	LV (low-	Unit
			speed	main)	speed	main)	voltage main)		
			Mo	ode	Mo	ode	Mo	ode	
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp hold time (from SCKp↓) ^{Note 2}	tksi1	$\begin{array}{l} 4.0 \; V \leq EV_{DD} \leq 5.5 \; V, 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$	19		19		19		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	19		19		19		ns
		$\begin{array}{l} 2.4 \ V \leq EV_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	19		19		19		ns
					19		19		ns
Delay time from SCKp↑ to SOp output ^{Note 2}	tkso1	$\begin{array}{l} 4.0 \; V \leq EV_{DD} \leq 5.5 \; V, 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$		25		25		25	ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$		25		25		25	ns
		$\begin{array}{l} 2.4 \ V \leq EV_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$		25		25		25	ns
		$ \begin{array}{l} 1.8 \ V \leq EV_{DD} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note } 3}, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array} $				25		25	ns

- **Notes** 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
 - 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **3.** Use it with $EV_{DD} \ge V_b$.
- Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (32-pin to 52pin products)/EV_{DD} tolerance (64-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.



CSI mode connection diagram (during communication at different potential)



- **Remarks 1.** R_b[Ω]:Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage
 - 2. p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM and POM number (g = 1)
 - 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01)



(T _A = –40 to +85	5°C, 1.8 \	$l \leq EV_{DD} = V_{DD} \leq 5.$	5 V, Vss = EVss = 0	V)						(1/2)
Parameter	Symbol	Conditions			high- main) ode	LS (low main)	/-speed mode	LV (voltage mo	low- e main) ode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time Note 1	tkCY2	$4.0 V \leq EV_{DD} \leq 5.5 V.$	20 MHz < fмск ≤ 24 MHz	12/fмск						ns
		$2.7 V \le V_b \le 4.0 V$	8 MHz < fмск ≤ 20 MHz	10/fмск						ns
			4 MHz < fмcк ≤ 8 MHz	8/fмск		16/fмск				ns
			fмск≤4 MHz	6/fмск		10/fмск		10/ f мск		ns
		$2.7 V \le EV_{DD} < 4.0 V$,	20 MHz < fмск ≤ 24 MHz	16/fмск						ns
		$2.3V{\leq}V_b{\leq}2.7V$	16 MHz < fмск ≤ 20 MHz	14/ f мск						ns
			8 MHz < fмск ≤ 16 MHz	12/fмск						ns
			4 MHz < fмск ≤ 8 MHz	8/f мск		16/fмск				ns
			fмск ≤4 MHz	6/ f мск		10/fмск		10/fмск		ns
		$2.4 V \le EV_{DD} < 3.3 V$,	20 MHz < fмск ≤ 24 MHz	36/f мск						ns
	$1.6 V \le V_b \le 2.0 V$	$16 \text{ MHz} < f_{MCK} \le 20 \text{ MHz}$	32/fмск						ns	
		8 MHz < fмск ≤ 16 MHz	26/fмск						ns	
			4 MHz < fмск ≤ 8 MHz	16/fмск		16/fмск				ns
			fмск≤4 MHz	10/fмск		10/fмск		10/fмск		ns
		$1.8 V \le EV_{DD} < 3.3 V$,	4 MHz < fмск ≤ 8 MHz			16/fмск				ns
	$1.6 V \le V_b \le 2.0 V^{Note 2}$	fмск≤4 MHz			10/fмск		10/fмск		ns	
SCKp high-/low-level width	p high-/low-level t _{KH2} , 4.0 V ≤ EV _{DD} ≤ 5.5 t _{KL2}	$4.0~V \leq EV_{\text{DD}} \leq 5.5~V$	$V, 2.7 \text{ V} \le V_b \le 4.0 \text{ V}$	tксү2/2 – 12		tксү2/2 - 50		tксү2/2 - 50		ns
		$2.7 \text{ V} \le EV_{\text{DD}} < 4.0 \text{ V}, 2.3 \text{ V} \le V_{\text{b}} \le 2.7 \text{ V}$		tксү2/2 – 18		tксү2/2 - 50		tксү2/2 – 50		ns
		$2.4 \text{ V} \le \text{EV}_{\text{DD}} < 3.3 \text{ V}$	$V_{\rm t}, 1.6 \ V \le V_{\rm b} \le 2.0 \ V_{\rm b}$	tkcy2/2		tксү2/2 - 50		tkcy2/2 - 50		ns
		$1.8 V \le EV_{DD} < 3.3 V$ $1.6 V \le V_b \le 2.0 V^{Not}$	/, te 2			tксү2/2 - 50		tkcy2/2		ns
Slp setup time	tsik2	$4.0 V \le EV_{DD} \le 5.5 V$	$V_{\rm h} = 2.7 \text{V} \le V_{\rm h} \le 4.0 \text{V}$	1/fмск +		1/fмск +		1/fмск +		ns
(to SCKp↑) Note 3			,	20		30		30		
		$2.7 \text{ V} \le \text{EV}_{\text{DD}} < 4.0 \text{ V}$	$V, 2.3 V \le V_b \le 2.7 V$	1/fмск + 20		1/fмск + 30		1/fмск + 30		ns
		$2.4 \text{ V} \le \text{EV}_{\text{DD}} < 3.3 \text{ V}$	V , 1.6 V \leq V _b \leq 2.0 V	1/fмск + 30		1/fмск + 30		1/fмск + 30		ns
		$1.8 V \le EV_{DD} < 3.3 V$ $1.6 V \le V_b \le 2.0 V^{Not}$	/, te 2			1/fмск + 30		1/fмск + 30		ns
SIp hold time (from SCKp↑) ^{Note 4}	tksi2	$4.0 \text{ V} \le \text{EV}_{\text{DD}} < 5.5 \text{ V}$	$V, 2.7 \text{ V} \le V_b \le 4.0 \text{ V}$	1/fмск+ 31		1/fмск + 31		1/fмск + 31		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD}} < 4.0 \text{ V}$	$V_{\rm y}, 2.3 \ V \le V_b \le 2.7 \ V_b$	1/fмск+ 31		1/fмск + 31		1/fмск + 31		ns
		$2.4 \text{ V} \le \text{EV}_{\text{DD}} < 3.3 \text{ V}$	$V_{\rm t}, 1.6 \ V \le V_b \le 2.0 \ V_b$	1/fмск+ 31		1/fмск+ 31		1/fмск + 31		ns
		$1.8 \text{ V} \le \text{EV}_{\text{DD}} < 3.3 \text{ V}$ $1.6 \text{ V} \le \text{V}_{b} \le 2.0 \text{ V}^{\text{Not}}$	/, te 2			1/fмск + 31		1/fмск + 31		ns

(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

(Notes, Caution and Remarks are listed on the next page.)

- **Notes 1.** The first clock pulse is generated after this period when the start/restart condition is detected.
 - 2. The maximum value (MAX.) of the is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.
- **Remark** The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: C_b = 400 pF, R_b = 2.7 k Ω



(3) I^2C fast mode plus

 $(T_A = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le EV_{DD} = V_{DD} \le 5.5 \text{ V}, \text{ Vss} = EV_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (hig main)	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode	
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscl	$\begin{array}{ c c c } \mbox{Fast mode plus:} & 2.7 \ \mbox{V} \leq \mbox{EV}_{\mbox{DD}} \leq 5.5 \ \mbox{V} \\ \mbox{f}_{\mbox{CLK}} \geq 10 \ \mbox{MHz} \end{array}$	0	1000	_	_	_	_	kHz
Setup time of restart condition	tsu:sta	$2.7 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$	0.26		_	-	_	_	μs
Hold time ^{Note 1}	thd:sta	$2.7~V \leq EV_{DD} \leq 5.5~V$	0.26			_	_	_	μs
Hold time when SCLA0 = "L"	t∟ow	$2.7 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$	0.5		—				μs
Hold time when SCLA0 = "H"	tнigн	$2.7 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$	0.26		_	_	-	_	μs
Data setup time (reception)	tsu:dat	$2.7 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$	50		-	-	-	_	μs
Data hold time (transmission) ^{Note 2}	thd:dat	$2.7 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$	0	0.45	_	_	_	_	μs
Setup time of stop condition	tsu:sto	$2.7 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$	0.26		_	_	-	_	μs
Bus-free time	tBUF	$2.7 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$	0.5			_	_	_	μs

- Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.
 - 2. The maximum value (MAX.) of the during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.
- Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.
- **Remark** The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode plus: C_b = 120 pF, R_b = 1.1 k Ω

IICA serial transfer timing





3.5 Peripheral Functions Characteristics

AC Timing Test Points



3.5.1 Serial array unit

(1) During communication at same potential (UART mode) ($T_A = -40$ to +105°C, 2.4 V $\leq EV_{DD} = V_{DD} \leq 5.5$ V, Vss = EVss = 0 V)

Parameter	Symbol	Conditions		HS (high-spee	Unit	
				MIN.	MAX.	
Transfer rate Note 1					fмск/12	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 2}$		2.0	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The maximum operating frequencies of the CPU/peripheral hardware clock (fcLK) are:

HS (high-speed main) mode: 24 MHz ($2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$) 16 MHz ($2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remarks 1. q: UART number (q = 0), g: PIM and POM number (g = 1)

 fmcκ: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

(2/2)

Parameter	Symbol	Conditions	HS (high-spee	ed main) Mode	Unit
			MIN.	MAX.	
SIp setup time	tsik1	$4.0 \ V \le EV_{\text{DD}} \le 5.5 \ V, \ 2.7 \ V \le V_{\text{b}} \le 4.0 \ V,$	162		ns
(to SCKp↑) ^{Note 1}		C_b = 30 pF, R_b = 1.4 k Ω			
		$2.7 \text{ V} \le \text{EV}_{\text{DD}} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$	354		ns
		C_b = 30 pF, R_b = 2.7 k Ω			
		$2.4 \text{ V} \le \text{EV}_{\text{DD}} < 3.3 \text{ V}, \ 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$	958		ns
		C_b = 30 pF, R_b = 5.5 k Ω			
SIp hold time	tksi1	$4.0 \ V \leq EV_{\text{DD}} \leq 5.5 \ V, \ 2.7 \ V \leq V_{\text{b}} \leq 4.0 \ V,$	38		ns
(from SCKp↑) ^{Note 1}		C_b = 30 pF, R_b = 1.4 k Ω			
		$2.7 \text{ V} \le \text{EV}_{\text{DD}}$ < 4.0 V, 2.3 V $\le \text{V}_{\text{b}} \le 2.7 \text{ V}$,	38		ns
		C_b = 30 pF, R_b = 2.7 k Ω			
		$2.4 \text{ V} \le \text{EV}_{\text{DD}} < 3.3 \text{ V}, \ 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$	38		ns
		C_b = 30 pF, R_b = 5.5 k Ω			
Delay time from SCKp↓ to	tkso1	$4.0 \; V \leq EV_{\text{DD}} \leq 5.5 \; V, \; 2.7 \; V \leq V_{\text{b}} \leq 4.0 \; V,$		200	ns
SOp output Note 1		C_b = 30 pF, R_b = 1.4 k Ω			
		$2.7 \text{ V} \leq \text{EV}_{\text{DD}} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V},$		390	ns
		C_b = 30 pF, R_b = 2.7 k Ω			
		$2.4 \text{ V} \leq \text{EV}_{\text{DD}} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V},$		966	ns
		C_b = 30 pF, R_b = 2.7 k Ω			
SIp setup time	tsik1	$4.0 \; V \leq EV_{\text{DD}} \leq 5.5 \; V, \; 2.7 \; V \leq V_{\text{b}} \leq 4.0 \; V,$	88		ns
(to SCKp↓) ^{Note}		C_b = 30 pF, R_b = 1.4 k Ω			
		$2.7 \text{ V} \leq \text{EV}_{\text{DD}} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V},$	88		ns
		C_b = 30 pF, R_b = 2.7 k Ω			
		$2.4 \ V \leq EV_{\text{DD}} < 3.3 \ V, \ 1.6 \ V \leq V_{\text{b}} \leq 2.0 \ V,$	220		ns
		C_b = 30 pF, R_b = 5.5 k Ω			
SIp hold time	tksi1	$4.0~V \leq EV_{\text{DD}} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$	38		ns
(from SCKp↓) Note 2		C_b = 30 pF, R_b = 1.4 k Ω			
		$2.7 \text{ V} \leq \text{EV}_{\text{DD}} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V},$	38		ns
		C_b = 30 pF, R_b = 2.7 k Ω			
		$2.4~V \leq EV_{\text{DD}} < 3.3~V,~1.6~V \leq V_b \leq 2.0~V,$	38		ns
		C_b = 30 pF, R_b = 5.5 k Ω			
Delay time from SCKp↑ to	tkso1	$4.0~V \leq EV_{\text{DD}} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$		50	ns
SOp output Note 2		C_b = 30 pF, R_b = 1.4 k Ω			
		$2.7 \text{ V} \leq \text{EV}_{\text{DD}} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V},$		50	ns
		C_{b} = 30 pF, R_{b} = 2.7 k Ω			
		$2.4 \ V \le EV_{\text{DD}} < 3.3 \ V, \ 1.6 \ V \le V_{\text{b}} \le 2.0 \ V,$		50	ns
		C_b = 30 pF, R_b = 5.5 k Ω			

(Notes, Caution and Remarks are listed on the page after the next page.)



- Notes 1. Transfer rate in the SNOOZE mode : MAX. 1 Mbps
 - **2.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **4.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Caution Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (V_{DD} tolerance (32- to 52-pin products)/EV_{DD} tolerance (64-pin products)) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.



CSI mode connection diagram (during communication at different potential)

Remarks 1. $R_b[\Omega]$:Communication line (SOp) pull-up resistance,

 $C_b[F]$: Communication line (SOp) load capacitance, $V_b[V]$: Communication line voltage

- **2.** p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1),
 - g: PIM and POM number (g = 1)
- 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))



3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

		Reference Voltage	
	Reference voltage (+) = AVREFP	Reference voltage (+) = VDD	Reference voltage (+) = V _{BGR}
Input channel	Reference voltage (-) = AVREFM	Reference voltage (-) = Vss	Reference voltage (-) = AVREFM
ANIO, ANI1	-	Refer to 3.6.1 (3).	Refer to 3.6.1 (4).
ANI16 to ANI23	Refer to 3.6.1 (2).		
Internal reference voltage Temperature sensor output voltage	Refer to 3.6.1 (1) .		_

(1) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : internal reference voltage, and temperature sensor output voltage

Parameter	Symbol	Conditio	ns	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$2.4 \text{ V} \leq AV_{\text{REFP}} \leq 5.5 \text{ V}$		1.2	±3.5	LSB
Conversion time	version time t _{CONV} 10-bit resolution		$3.6~V \leq V_{\text{DD}} \leq 5.5~V$	2.375		39	μs
		Target pin: Internal reference 2 voltage, and temperature 2 sensor output voltage (HS 2 (high-speed main) mode) 1 10-bit resolution 1	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	3.5625		39	μs
			$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$1.8 \text{ V} \le \text{AV}_{\text{REFP}} \le 5.5 \text{ V}$			±0.25	%FSR
Full-scale error ^{Notes 1, 2}	Efs	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$1.8 \text{ V} \leq AV_{\text{REFP}} \leq 5.5 \text{ V}$			±0.25	%FSR
Integral linearity error	ILE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$1.8 \text{ V} \le \text{AV}_{\text{REFP}} \le 5.5 \text{ V}$			±2.5	LSB
Differential linearity error	DLE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$1.8 \text{ V} \leq AV_{\text{REFP}} \leq 5.5 \text{ V}$			±1.5	LSB
Analog input voltage	VAIN	Internal reference voltage (2.4 V \leq VDD \leq 5.5 V, HS (high-speed main) mode)			VBGR Note 4		V
		Temperature sensor output volt (2.4 V \leq VDD \leq 5.5 V, HS (high-	tage speed main) mode)	VTMPS25 Note 4			V

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD} = \text{V}_{DD} \le 5.5 \text{ V}, 2.4 \text{ V} \le \text{AV}_{REFP} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS} = 0 \text{ V}, \text{Reference voltage (+)} = \text{AV}_{REFP}, \text{Reference voltage (-)} = \text{AV}_{REFM} = 0 \text{ V})$

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- **2.** This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. When AV_{REFP} < V_{DD}, the MAX. values are as follows. Overall error: Add ±1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}. Zero-scale error/Full-scale error: Add ±0.05%FSR to the MAX. value when AV_{REFP} = V_{DD}. Integral linearity error/ Differential linearity error: Add ±0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.
- 4. Refer to 3.6.2 Temperature sensor/internal reference voltage characteristics.

3.7.2 Internal voltage boosting method

(1) 1/3 bias method

(T_A = -40 to +105°C, 2.4 V \leq V_DD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
LCD output voltage variation range	V _{L1}	C1 to C4 ^{Note 1} = 0.47 μF	VLCD = 04H	0.90	1.00	1.08	V
			VLCD = 05H	0.95	1.05	1.13	V
			VLCD = 06H	1.00	1.10	1.18	V
			VLCD = 07H	1.05	1.15	1.23	V
			VLCD = 08H	1.10	1.20	1.28	V
			VLCD = 09H	1.15	1.25	1.33	V
			VLCD = 0AH	1.20	1.30	1.38	V
			VLCD = 0BH	1.25	1.35	1.43	V
			VLCD = 0CH	1.30	1.40	1.48	V
			VLCD = 0DH	1.35	1.45	1.53	V
			VLCD = 0EH	1.40	1.50	1.58	V
			VLCD = 0FH	1.45	1.55	1.63	V
			VLCD = 10H	1.50	1.60	1.68	V
			VLCD = 11H	1.55	1.65	1.73	V
			VLCD = 12H	1.60	1.70	1.78	V
			VLCD = 13H	1.65	1.75	1.83	V
Doubler output voltage	VL2	C1 to C4 ^{Note 1} = 0.47 μ F		2 V∟1 –0.1	2 VL1	2 V _{L1}	V
Tripler output voltage	VL4	C1 to $C4^{\text{Note 1}} = 0.47 \mu\text{F}$		3 V∟1 –0.15	3 VL1	3 VL1	V
Reference voltage setup time Note 2	tvwait1			5			ms
Voltage boost wait time ^{Note 3}	tvwait2	C1 to C4 ^{Note 1} = 0.47 μ F		500			ms

Notes 1. This is a capacitor that is connected between voltage pins used to drive the LCD.

C1: A capacitor connected between CAPH and CAPL

C2: A capacitor connected between $V_{\mbox{\tiny L1}}$ and GND

C3: A capacitor connected between $V_{\mbox{\tiny L2}}$ and GND

C4: A capacitor connected between $V_{{\mbox{\tiny L4}}}$ and GND

C1 = C2 = C3 = C4 = 0.47 μ F \pm 30%

2. This is the time required to wait from when the reference voltage is specified by using the VLCD register (or when the internal voltage boosting method is selected [by setting the MDSET1 and MDSET0 bits of the LCDM0 register to 01B] if the default value reference voltage is used) until voltage boosting starts (VLCON = 1).

3. This is the wait time from when voltage boosting is started (VLCON = 1) until display is enabled (LCDON = 1).

3.11 Timing Specifications for Switching Flash Memory Programming Modes (T_A = -40 to +105°C, 2.4 V \leq EV_{DD} = V_{DD} \leq 5.5 V, V_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	tsuinit	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	tsu	POR and LVD reset must be released before the external reset is released.	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	tно	POR and LVD reset must be released before the external reset is released.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.
- **Remark** tsuinit: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.
 - $t_{\text{su:}}$ Time to release the external reset after the TOOL0 pin is set to the low level
 - the: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)



4.2 44-pin Products

R5F10RF8AFP, R5F10RFAAFP, R5F10RFCAFP R5F10RF8GFP, R5F10RFAGFP, R5F10RFCGFP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP44-10x10-0.80	PLQP0044GC-A	P44GB-80-UES-2	0.36



NOTE

Each lead centerline is located within 0.20 mm of its true position at maximum material condition.

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у

ZD

ZE

0.10

1.00

1.00



4.4 52-pin Products

R5F10RJ8AFA, R5F10RJAAFA, R5F10RJCAFA R5F10RJ8GFA, R5F10RJAGFA, R5F10RJCGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP52-10x10-0.65	PLQP0052JA-A	P52GB-65-GBS-1	0.3



2.Dimension "X3" does not include trim offset.

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е

x y 0.65

0.10

